Design and modeling of membrane-based evaporative cooling devices for thermal management of high heat fluxes

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Abstract

We present a high-heat-flux cooling device for advanced thermal management of electronics. The device incorporates nanoporous membranes supported on microchannels to enable thin film evaporation. The underlying concept takes advantage of the capillary pressure generated by small pores in the membrane, and minimizes the viscous loss by reducing the membrane thickness. The heat transfer and fluid flow in the device were modeled to determine the effect of different geometric parameters. With the optimization of various parameters, the device can achieve a heat transfer coefficient in excess of 0.05 kW/cm²-K while dissipating a heat flux of 1 kW/cm². When applied to power electronics, such as GaN high electron mobility transistors, this membrane-based evaporative cooling device can lower the near junction temperature by more than 40 K compared to contemporary single-phase microchannel coolers.
Introduction

Thermal management has become a critical issue in the semiconductor industry due to the increasing power density of microprocessors, laser diodes and power amplifiers [1-3]. One of the most pressing challenges in current and next-generation electronics is heat removal of wide band gap semiconductors based on gallium nitride (GaN) and silicon carbide (SiC), for high-power radiofrequency (RF) applications [4]. For example, monolithic microwave integrated circuits (MMICs) based on GaN high electron mobility transistor (HEMT) technology are devices of particular importance for microwave applications. With a standard layout [5] (Figure 1(a) and (b)), and a modest power density of 5 W/mm, the heat flux generated over the gate area in the RF MMIC highlighted by the red stripes in Figure 1(a) (0.5 μm × 150 μm each), can be as high as 1000 kW/cm² [6]. Even on the backside of the die, the heat flux can still be > 1 kW/cm² [6]. Such high fluxes are likely to induce high temperatures in the gate area, which can reduce the lifetime and the reliability of the GaN HEMT devices [4]. To lower the near junction temperature and handle the high heat loads, new cooling methods are needed.

Many approaches have been pursued, including single-phase forced convection, pool-boiling and flow-boiling. Single-phase cooling has been experimentally demonstrated up to 1.25 kW/cm² in microchannels [7], but it requires a large temperature difference and high pumping power [8]. Meanwhile, phase change cooling can be more effective, taking advantage of the enthalpy of vaporization and lowering the pumping power requirement. However, phase-change cooling mechanisms, such as pool-boiling, are fundamentally limited by the critical heat flux (CHF), where ~ 400 W/cm² has been demonstrated [9, 10]. On the other hand, while flow boiling is promising for reducing the pumping power, and achieving a higher HTC and heat flux, flow instabilities [7], temperature and pressure fluctuations [8] are still major concerns.
To address these issues in flow boiling, previous studies have investigated into techniques such as dynamic active flow control [11], integrating microstructures [12], flow re-entrance [13], inlet restriction [14] and phase separation [15-17]. Particularly, in phase separation approaches, liquid is actively pumped into microchannels covered by a hydrophobic nanoporous membrane and vapor is vented through the pores. In these cases, we note that the phase change occurs underneath the membrane, which can create an additional thermal resistance since the transmission probability for vapor molecules to escape the nanopores can be considerably less than 1 [18].

Another approach that makes use of the enthalpy of vaporization and naturally separates the two phases is the implementation of thin film evaporation [19, 20]. In this case, the thermal resistance across the evaporating liquid is minimized by maintaining a thin liquid film across which the overall thermal transport is significantly enhanced. However, active pumping of liquid into the evaporating thin film (< 1 μm thick [21]) over large regions can be impractical due to high pressure drops, requiring significant pumping powers. Consequently, to facilitate passive liquid flow, nano/micro wicks have been utilized to generate capillary pressure to draw liquid into the evaporating thin film region. For example, evaporation from titanium pillar arrays [22] and alumina nanoporous membranes [20, 23] has been studied in previous work.

However, as the characteristic wicking size is made smaller, the capillary pressure and the viscous loss both increase. As a result, in typical microfluidic implementations of thin film evaporation, these two parameters are strongly coupled, limiting the overall performance if the cooling device is not designed appropriately.

To decouple the viscous stress and the capillary pressure, we propose a membrane-based cooling device that leverages evaporation in a thin (thickness < 1 μm) nanoporous membrane (pore diameter ~ 100 nm) supported by microchannels (characteristic dimension < 10 μm), as shown in
Figure 1(c). During operation, the liquid is drawn across the microchannels as it is wicked into the nanopores of the membrane, where it absorbs heat, evaporates into a pure vapor ambient and eventually condenses at a condenser and is circulated back to the inlet of the cooling device (Figure 1(c) and (d)). The heat supplied for evaporation conducts across the substrate to the microchannel walls, then through the membrane to the liquid-vapor interface, where evaporation takes place (Figure 1(c)). The device relies on the capillary pressure supplied by the nanopores to drive the flow, and takes advantage of phase change to dissipate significant amounts of heat. This is done while minimizing the viscous losses for the flow across the microchannels and the membrane, and the overall thermal resistance across the liquid. Consequently, the device can potentially deliver high heat fluxes for cooling, with low overall temperature differences as well as minimal pumping power requirements. The reliance on the capillary pressure within the pores to drive the flow also results in a self-regulating device, which may be able to better address challenges associated with spatially-varying heat fluxes. This is particularly challenging in flow-boiling based approaches, due to pressure instabilities and flow mal-distribution, which is difficult to mitigate at the microscale.

In fact, designing such membrane-base evaporative cooling devices relies heavily on fundamental understanding of interfacial transport at the small scale. In this study, we carried out a detailed computational analysis to design the proposed cooling device, and investigated the overall heat and mass transfer during evaporation, where we carefully account for the sub-continuum and non-equilibrium effects of the vapor transport as opposed to using a constant temperature at the interface [16] or the traditional Schrage’s approach [24]. Using this analysis, we also identified the criteria for the selection of the most appropriate working fluid to deliver the highest performance. We then determined the thermal and hydraulic performance of the cooling device as a function of
different geometric parameters for design optimization. Subsequently, we demonstrated the use of this device for the thermal management of GaN HEMTs [2] (Figure 1(a) and (b)), to show significantly reduced near junction temperatures compared to the baseline performance using a contemporary cooling mechanism.

**Baseline Performance using Single Phase Cooling**

A common technique to cool GaN HEMTs is to use a single-phase microchannel cooler. For example, Calame *et al.* demonstrated that die-level heat transfer coefficients (HTCs) of 0.021 kW/cm²-K can be achieved with 1.9 L/min water flowing through copper microchannels [4]. With such microchannel coolers rejecting heat to a reservoir maintained at 25 °C, we simulated the heat conduction in the device to determine temperature and the heat flux distribution in the GaN HEMT (Figure 1(a) and (b)) using the finite element method in COMSOL Multiphysics [25], where the total number of elements was 4383224 and the relative tolerance for convergence was set as $10^{-6}$. The thermal conductivities of GaN and SiC ($k_{GaN}$ and $k_{SiC}$) and the thermal boundary resistance ($R_B$) between these layers, as a function of temperature, were taken into account as [26]:

\[
 k_{GaN} = 150 \left( \frac{T}{300 \text{ K}} \right)^{-1.4} \text{ (W/m-K)}
\]  
(1)

\[
 k_{SiC} = 420 \left( \frac{T}{300 \text{ K}} \right)^{-1.4} \text{ (W/m-K)}
\]  
(2)

\[
 R_B = 1.57 \times 10^{-15} \left( \frac{T}{1 \text{ K}} \right)^{2.76} \text{ (m²K/W)}
\]  
(3)

Using the typical heat fluxes encountered in GaN HEMT (1000 kW/cm² over the gate area) and the HTC achievable using single-phase microchannel cooling, the temperature profile for a quarter
of the die is shown in Figure 1(e), where the peak HEMT device temperature is found to be as high as 218 °C. Additionally, cooling heat fluxes > 1 kW/cm² are necessary for thermal management of GaN devices, as shown in Figure 1(f).

**Interfacial Transport and Coolant Selection**

To properly model the performance of our proposed cooling device, we analyzed transport across the liquid-vapor interface to determine the appropriate boundary condition at the evaporative surface of the cooling device. Traditionally, the interfacial heat transfer coefficient, $h_{in}$ is calculated using the Schrage equation [24]:

$$h_{in,Schrage} = \frac{2\bar{\sigma}}{2 - \bar{\sigma}} \frac{h_{fg}}{T_{in} - T_{\infty}} \sqrt{\frac{1}{2\pi R} \left( \frac{P_{eq}}{T_{in}^{1/2}} - \frac{P_{\infty}}{T_{\infty}^{1/2}} \right)} \tag{4}$$

where $\bar{\sigma}$ is the accommodation coefficient [27], $h_{fg}$ is the heat of vaporization, $R$ is the specific gas constant, $P_{eq}$ is the vapor pressure in equilibrium with the liquid, $T_{in}$ is the temperature at the interface, and $P_{\infty}$ and $T_{\infty}$ are the pressure and temperature of the vapor in the far field, respectively. However, it has been shown recently that the traditional approach does not account for momentum and energy conservation [28], which is crucial for the analysis of high flux evaporation.

To predict evaporation more accurately, Labuntsov and Kryukov developed the moment method to solve the Boltzmann transport equation governing the interfacial heat and mass transfer process [29], conserving mass, momentum and energy. In our recent study [18], we utilized this method to analyze evaporation from nanoporous structures. Our investigation of evaporation from nanopores takes into account the non-equilibrium effects and the deviation from classical kinetic theory. In addition, by considering the non-local effects arising from phase-change in nanoporous geometries, and the self-regulation of the shape and position of the liquid-vapor interface in response to
different operating conditions, we quantified the effects of various parameters and determine conditions suitable for evaporation. We found that the interfacial heat transfer is most efficient when the meniscus is pinned at the top of the pore with total accommodation ($\sigma = 1$ which is more likely for non-polar working fluids [30-33]). For $\sigma = 1$, the interfacial transport in nanopores did not depend significantly on the interface shape or the liquid pressure at the interface [34]. Instead, the interfacial HTC $h_{in}$, normalized over the pore cross-sectional area, varied only as a function of $T_{in}$ and $T_{\infty}$ as well as the porosity $\phi$ for pore diameter $\sim 100$ nm. We present the analysis for this particular case (pinning regime with total accommodation) as follows. (Discussion on more general cases can be found in Ref. [18].) For one unit cell, a cylindrical coordinate ($r, z$) system is defined in Figure 2(a). We set $z = 0$ at the pore outlet and the far field vapor at $z \rightarrow \infty$. We denote $\bar{\xi}$ as the velocity distribution function to yield the mass of molecules $dm$ in a unit volume at a certain velocity $u$, so that $dm = \bar{\xi} \, d^3u$. The distribution of molecules emitted out of the nanopore is given by the half Maxwellian [18, 29, 35]:

$$\bar{\xi} \bigg|_{z=0, u_z>0} = \rho_{sat} \frac{\exp\left(-\frac{u^2}{2RT_{in}}\right)}{(2\pi RT_{in})^{3/2}} \tag{5}$$

where $\rho_{sat}$ is the saturated vapor density at $T_{in}$. Since the evaporation in reality is a dynamic process, there is also a backflow of vapor molecules whose distribution at $z = 0$ is assumed to take the form [29]:

$$\bar{\xi} \bigg|_{z=0, u_z<0} = \rho_c \frac{\exp\left[\frac{-(u - u_z \hat{z})^2}{2RT_{\infty}}\right]}{(2\pi RT_{\infty})^{1/2}} \tag{6}$$
where \( \hat{z} \) is the unit vector in the \( z \)-direction, \( u_\infty \) is the bulk vapor velocity in the far field and \( \rho_c \) (yet to be calculated) denotes the effective density of vapor directed back to the pore outlet. The pressure on the top surface of the pore wall \( P_w \) can be determined as [18]:

\[
P_w = \int_{z = 0, r < r_p} \left( u \cdot \hat{r} \right)^2 d^3u
\]

(7)

where \( \hat{r} \) is the unit vector in the \( r \)-direction. In the far field \((z \to \infty)\), where thermodynamic equilibrium is again realized,

\[
\xi \bigg|_{z \to \infty} = \frac{\exp \left[ -\frac{(u - u_\infty \hat{z})^2}{2RT_\infty} \right]}{(2\pi RT_\infty)^{3/2}}
\]

(8)

where \( \rho_\infty \) is the vapor density in the far field. By conserving mass, momentum and energy \((\dot{m}, F_z\) and \(\dot{E})\) between the pore outlet and the far field within the unit cell, we have:

\[
\dot{m} = \phi \int_{z = 0} \xi \bigg|_{z = 0} u_z d^3u = \int \xi \bigg|_{z \to \infty} u_z d^3u
\]

(9)

\[
F_z = (1 - \phi) P_w + \phi \int \xi \bigg|_{z = 0} u_z^2 d^3u = \int \xi \bigg|_{z \to \infty} u_z^2 d^3u
\]

(10)

\[
\dot{E} = \phi \int \xi \bigg|_{z = 0} u_z \frac{u_z^2}{2} d^3u = \int \xi \bigg|_{z \to \infty} u_z \frac{u_z^2}{2} d^3u
\]

(11)

Eqn. (9), (10) and (11) contain three unknowns \((u_\infty, \rho_c, \rho_\infty)\). After non-dimensionalization, we can represent the solutions as [29]:

\[
\frac{u_\infty}{\sqrt{RT_m}} = f_1 \left( \frac{T_m}{T_\infty}, \phi \right)
\]

(12)

\[
\frac{\rho_c}{\rho_{sat}} = f_2 \left( \frac{T_m}{T_\infty}, \phi \right)
\]

(13)
\[
\frac{\rho_{\text{sat}}}{\rho_{\text{sat}}} = f_3 \left( \frac{T_{\text{m}}}{T_{\infty}}, \phi \right) 
\]

(14)

where \(f_1, f_2\) and \(f_3\) are all non-negative functions that come from solving Eqn. (9), (10) and (11).

The interfacial heat transfer coefficient out of the pore is then given as:

\[
h_{\text{in}} = \rho_{\text{sat}} h_{fg} \sqrt{RT_m} f_1 \left( \frac{T_{\text{m}}}{T_{\infty}}, \phi \right) f_3 \left( \frac{T_{\text{m}}}{T_{\infty}}, \phi \right)
\]

(15)

where \(h_{fg}\) is the enthalpy of vaporization. This result is plotted in Figure 2(b) for various fluids (water, methanol, pentane, R245fa and R134a) as a function of superheat \((T_{\text{in}} - T_{\infty})\), assuming \(T_{\infty} = 25^\circ\text{C}\) and \(\phi = 0.2\). We also show the effect of \(\phi\) on \(h_{\text{in}}\) normalized over the pore cross-sectional area, for a select working fluid (R134a) with different wall superheats in Figure 2(c).

Following this analysis, the interfacial heat flux is determined exclusively by the temperatures \(T_{\text{in}}\) and \(T_{\infty}\), and \(\phi\) for different nanoporous geometries, when divided by the product \(h_{fg} \rho_{\text{sat}} R^{1/2}\). We evaluate this product at \(25^\circ\text{C}\) and define it as the interfacial heat transfer factor. In order to compare different working fluids, we normalize \(h_{fg} \rho_{\text{sat}} R^{1/2}\) to the value for water and denote this ratio as:

\[
\Pi_1 = \frac{h_{fg} \rho_{\text{sat}} \sqrt{R}}{h_{fg,\text{water}} \rho_{\text{sat},\text{water}} \sqrt{R_{\text{water}}}}
\]

(16)

A larger \(\Pi_1\) indicates better interfacial heat transfer, which favors working fluids not only with a high \(h_{fg}\), but a high \(\rho_{\text{sat}}\) as well. On the other hand, since we rely on the capillary pressure to overcome the viscous loss, we define the liquid transport factor \(\Pi_2\) as done in heat pipes [36]:

\[
\Pi_2 = \frac{\sigma \rho h_{fg}}{\mu_l} \left/ \frac{\sigma_{\text{water}} \rho_{\text{water}} h_{fg,\text{water}}}{\mu_{\text{water}}} \right.
\]

(17)
where $\sigma$ is the surface tension, $\rho_l$ is the liquid density and $\mu_l$ is the liquid viscosity. As shown in Eqn. (17), $\Pi_2$ was obtained by normalizing with $\sigma \rho_l h_{fg}/\mu$ evaluated for water at 25 °C. The rationale behind using this figure of merit is that the capillary budget scales with $\sigma$ and the viscous loss scales with $\mu_l (\rho_l h_{fg})^{-1}$ given a heat removal rate. For the same rate of heat removal, a larger $\Pi_2$ indicates that the device is less prone to dry out. Table 1 shows these two figures of merit ($\Pi_1$ and $\Pi_2$) for select working fluids. Compared to other working fluids, R134a has a much higher $\Pi_1$. While $\Pi_2$ for R134a, R245fa, pentane, and methanol is comparable, it is significantly higher for water. We chose R134a to carry out device performance analysis, despite its higher risk of dry-out, due to its exceptionally high cooling potential. However, it should be noted that the same computational methodology is indeed applicable for any other working fluid, and can be utilized to determine device performance following a similar procedure. One other concern about R134a is related to its high saturated vapor pressure (665.8 kPa at 25 °C), which will place the interior of the device at a positive pressure relative to the exterior ambient. We anticipate that such a high operating pressure can be handled by a combination of package-level design coupled with die-level fusion bonding with heat treatment [37].

Table 1 Figures of merit for different working fluids: interfacial transport factor $\Pi_1$ and liquid transport factor $\Pi_2$ (both normalized to the properties of water).

<table>
<thead>
<tr>
<th>Fluids</th>
<th>Water</th>
<th>Methanol</th>
<th>Pentane</th>
<th>R245fa</th>
<th>R134a</th>
</tr>
</thead>
<tbody>
<tr>
<td>$\Pi_1$</td>
<td>1</td>
<td>3.416</td>
<td>6.748</td>
<td>10.56</td>
<td>42.95</td>
</tr>
<tr>
<td>$\Pi_2$</td>
<td>1</td>
<td>0.1909</td>
<td>0.09320</td>
<td>0.04345</td>
<td>0.04504</td>
</tr>
</tbody>
</table>
Device-Level Model Description

We modeled the pressure drop and heat transfer for the entire cooling device, after choosing R134a as the coolant and determining the pore-averaged evaporative boundary condition $h_{in}$ as a function of $T_{in}$, $T_\infty$ and $\phi$. The pressure drop in the microchannels is determined as:

$$\frac{dP_l}{dx} = -\frac{2f \text{ Re}}{D_h^2} \mu_l V_l$$ (18)

where $P_l$ is the pressure in the liquid phase, $x$ is the flow length, $D_h$ is the hydraulic diameter [38], $f \text{ Re}$ is the Poiseuille number which is depends on the channel aspect ratio (width: depth) $AR$ [39] and $V_l$ is the bulk liquid velocity in the channel. By mass conservation, we have:

$$\frac{dV_l}{dx} h_{ch} = -V_p \phi x$$ (19)

where $h_{ch}$ is the channel height and $V_p$ is the bulk liquid velocity in the pore, which is also determined by the heat flux being dissipated $\dot{q}^*$:

$$\dot{q}^* = \rho_l h_{fr} V_p \phi (1 - SF)$$ (20)

Here, $SF$ is the channel wall solid fraction $t_w$: $w + t_w$, where $w$ is the microchannel width and $t_w$ is the channel wall thickness (Figure 1(c)). The pressure drop in the pore is given by:

$$\frac{dP_p}{dx} = -\frac{32}{d_p^2} \mu_l V_p$$ (21)

where $d_p$ is the pore diameter. The largest pressure drop in the cooling device is then:

$$\Delta P = \int_0^{l_2} \frac{2f \text{ Re}}{D_h^2} \mu_l V_l dx + \int_0^{l_2} \frac{32}{d_p^2} \mu_l V_p dx$$ (22)
where \( l_{ch} \) is the microchannel length and \( t \) is the membrane thickness. Assuming that R134a perfectly wets the pore due to its low surface tension, the capillary pressure is:

\[
P_c = \frac{4\sigma}{d_p}
\]  
(23)

We define a dimensionless pressure budget \( P_B^* \) as the difference between the capillary pressure and the total pressure drop normalized over the capillary pressure:

\[
P_B^* = \frac{P_c - \Delta P}{P_c}
\]  
(24)

For operating conditions with \( P_B^* < 0 \), the cooling device will dry out due to insufficient liquid supply to the evaporating region.

The heat transfer in the proposed device can be analyzed as a two-dimensional problem, due to the periodic geometry of the cooling device (Figure 1(c)). Figure 3(a) depicts the boundary conditions for a unit cell, marked by the dotted box in Figure 1(c). The governing equation for the steady-state heat conduction across the cooling device is:

\[
\nabla \cdot (k_i \nabla T) = 0
\]  
(25)

where \( T \) is the temperature across the unit cells, \( i = 1, 2, 3, 4 \). \( k_1, k_2, k_3 \) and \( k_4 \) denote the thermal conductivity of the substrate, the channel wall, the porous membrane and the working fluid, respectively. The cooling device was designed in silicon to take advantage of the wide range of microfabrication techniques available for silicon substrates. However, the modeling done in this work can be readily translated to other substrate materials. The temperature dependence of thermal conductivities of silicon and R134a is taken into account as described in Ref. [26] and [40]. The thermal conductivity of the microchannel walls and the nanoporous membrane \( (k_2 \text{ and } k_3) \) also
depends on the limiting dimension of these structures [41]. Therefore, in this study, the size
dependence of \( k_2 \) and \( k_3 \) was interpolated from the analyses carried out in Ref. [41].

In Figure 3(a), a uniform heat flux \( \dot{q}'' \) is applied at the bottom of the unit cell, while a pore-averaged
 evaporative heat transfer coefficient \( h_{\text{in}} \) is applied on top of the membrane considering the
membrane porosity \( \phi \). All other boundaries are assumed to be adiabatic and \( T_\infty \) is set at 25 °C. Note
that a portion of the silicon substrate (1 μm) is also included in the heat transfer model to account
for the constriction resistance from the silicon substrate to the channel walls. Eqn. (25) was solved
iteratively using finite element method in COMSOL Multiphysics due to the nonlinearity arising
from the temperature dependence of \( k_i \) (\( i = 1, 2, 3, 4 \)) and \( h_{\text{in}} \). The total number of elements in
COMSOL was 13259 in this case and the relative tolerance was set to be \( 10^{-6} \).

Note that heat convection in the liquid phase is neglected in this study. To justify this assumption,
we define a modified Péclet number:

\[
\text{Pe} = \frac{\rho_c c_p V \phi}{\left[ k_2 SF + k_4 (1 - SF) \right] / h_{ch}}
\]  

(26)

Here, \( c_p \) is the specific heat capacity of the liquid. The denominator is derived from the combined
thermal conductance of the liquid and the channel wall and the numerator corresponds to the
energy carried by the liquid flow in the direction perpendicular to the substrate. This Péclet number
compares the heat transfer from the substrate to the membrane due to convection and conduction.
As long as \( \text{Pe} \ll 1 \), the heat convection in the liquid phase can be neglected. Furthermore,
ignoring heat convection only underestimates the device cooling performance, which adds to the
safety factor of the proposed design.
Results and Discussion

For the GaN HEMT device shown in Figure 1(a), $l_{ch} = 700 \text{ μm}$ (Figure 1(d)). To calculate the pressure budget, we first set $\dot{q}'' = 1 \text{ kW/cm}^2$, $\phi = 0.25$, $d_p = 100 \text{ nm}$, the membrane thickness $t = 300 \text{ nm}$, $w = 5 \text{ μm}$, $AR = 1$, $SF = 0.2$. $P_B^*$ was then found to be 0.3423 using Eqn. (18), Eqn. (23) and Eqn. (24), which indicates that dry-out will not occur for these operating conditions. The temperature profile in the cooling device is plotted in Figure 3(b), which allows evaluation of the overall HTC of the cooling device:

$$h_d = \frac{\dot{q}''}{T_b - T_w}$$  \hspace{1cm} (27)

where $T_b$ is the average temperature at the base of the unit cell (Figure 3 (a)). In this reference case, $h_d = 0.0441 \text{ kW/cm}^2\text{-K}$. Also, we verified that $Pe = 0.034$ with all properties evaluated at 40 °C, which suggests that convection can be neglected. For comparison with the results obtained for R134a, we also simulated the device performance with water as the working fluid with total accommodation, which gives $h_d = 0.0155 \text{ kW/cm}^2\text{-K}$, supporting our rationale for this coolant selection. Even though water has a very large enthalpy of vaporization, its low vapor density limits the interfacial heat transfer.

Apart from the reference case study, a parametric sweep of various device geometries was also conducted, where each geometric parameter, namely $\phi$, $d_p$, $t$, $w$, $AR$ and $SF$ were varied independently from the reference case described above, and the corresponding effects on the heat transfer and pressure drop are shown in Figure 4(a) – (f).

In Figure 4(a), as the membrane becomes more porous by maintaining a constant pore diameter and increasing the number of pores per unit area, $h_d$ first increases due to a larger available
evaporation area. Then, it decreases due to a decrease in the effective thermal conductivity of the membrane. Furthermore, $P_B^*$ increases with $\phi$, since the mass flux in a single pore decreases with an increase in $\phi$.

In Figure 4(b), for all the pore diameters considered, the thermal resistance across the liquid confined within the pore is negligible. However, for a fixed porosity, a larger $d_p$ results in a larger pore spacing, which leads to a higher effective membrane thermal conductivity due to more diffusive thermal transport within the membrane [41]. This results in enhancing the overall heat transfer. On the other hand, since the viscous loss inside the pore scales with $1/d_p^2$ and the capillary pressure scales with $1/d_p$, $P_B^*$ initially increases as $d_p$ increases since the decrease in the viscous loss has a greater effect than the loss in capillary pressure. However, for larger $d_p$, the viscous loss in the pore is much lower than the loss in the microchannel, and therefore does not affect the total pressure drop significantly. Consequently, a continued decrease in the capillary pressure due to a larger $d_p$ causes a decrease in $P_B^*$.

Figure 4(c) shows that as the membrane becomes thicker, the spreading resistance within the membrane becomes smaller, which facilitates improvement in the overall heat transfer. However, this effect plateaus as the spreading resistance contributes less to the total thermal resistance while $t$ increases. $P_B^*$ decreases rapidly for thicker membranes due to larger viscous losses for flow through the nanopores.

In Figure 4(d), with increasing channel width, $w$, the spreading resistance in the membrane increases, which results in performance degradation. Meanwhile, the pressure drop in the microchannels becomes smaller, which enhances $P_B^*$. However, $P_B^*$ becomes insensitive to variation in $w$ once the pressure-drop is mostly due to the flow across the membrane.
A larger $AR$ corresponds to a larger channel height, which results in larger thermal resistance and consequently reduces $h_d$, shown in Figure 4(e). With a decrease in the flux in the microchannels due to larger flow cross-section area of the channel, $P_B$ increases rapidly until the viscous loss across the membrane dominates.

In Figure 4(f), as $SF$ increases, the membrane area available to wick liquid decreases. Therefore, the flux in a single pore becomes larger, resulting in a larger pressure drop across the membrane, decreasing $P_B^*$. An increasing $SF$ also decreases the thermal resistance through the channel wall and within the membrane, so $h_d$ is initially enhanced. However, because the net evaporation area becomes smaller, $h_d$ decreases when SF is relatively large.

After understanding the effect of each geometric parameter, a global optimization was performed in the design space (containing all of the geometric parameters), evaluating the heat transfer and pressure drop of each design with $\dot{q}'' = 1 \text{ kW/cm}^2$ (Figure 5). The criteria for the optimization is determined based on the application of this technology. For this current study, among parametric combinations satisfying $P_B^* > 0.6$, we selected a design which provides the highest $h_d$. With $P_B^* > 0.6$, we aim to mitigate the risk of dry-out caused by fabrication uncertainties, such as merging of nanopores and variation of channel sizes, and non-uniform heat fluxes at the backside of the die (up to $\sim 2 \text{ kW/cm}^2$). The optimum design parameters are given as $\phi = 0.4$, $d_p = 120 \text{ nm}$, $t = 450 \text{ nm}$, $w = 4 \mu\text{m}$, $AR = 2.5$, $SF = 0.25$, which results in $h_d = 0.0541 \text{ kW/cm}^2\text{-K}$. Note that this $h_d$ was obtained only for a constant and uniform heat flux ($\dot{q}'' = 1 \text{ kW/cm}^2$) dissipated by the evaporative cooling mechanism. Due to the temperature dependence of material properties ($k_i, i = 1, 2, 3, 4$) and interfacial transport ($h_{in}$), $h_d$ also varies as a function of $\dot{q}''$ for the chosen geometric design (inset of Figure 5). Consequently, $h_d$ can serve as a non-linear boundary condition when modeling evaporative cooling for the entire GaN HEMT die.
Evaporative Cooling of GaN HEMT

To demonstrate the feasibility of this proposed device, we model the overall heat transfer by interfacing the GaN HEMT (Figures 1(a) and (b)) with the optimized evaporative cooling device via gold eutectic bonding. To account for the additional thermal resistance due to the gold eutectic bond, we included a 10 μm Au and 100 μm silicon layer between the cooling device and the backside of the SiC substrate of the GaN HEMT device. For this configuration, the net heat transfer was again evaluated using the finite element method in COMSOL Multiphysics, where the total number of elements was 4598448 and the relative tolerance for convergence was set as $10^{-6}$. The resulting steady state temperature profile across the GaN HEMT device is shown in Figure 6 (a). When compared with Figure 1(e), the benefit of implementation of an evaporative cooling device is clear. While the heat flux distribution at the backside of the die (Figure 6(b)) is similar to the case with microchannel cooler (Figure 1(f)), the near-junction temperature is reduced by 46 K for the chosen GaN HEMT device by implementing the evaporative cooling device.

Although the proposed design shows promise in high flux heat dissipation, its cooling performance largely depends on the accommodation coefficient $\tilde{\sigma}$ of the liquid-vapor interface and may be subject to non-idealities of the working fluids (e.g., $\tilde{\sigma}$ is reported to be considerably less than 1 for water in literature [27]). In addition, for practical implementation, non-evaporative contamination in the system can also decrease the effective $\tilde{\sigma}$ and may eventually clog the device, which is a concern for every evaporation-based system. In our proposed design (Figure 1(d)), there is a constant liquid flow along the channel underneath the pores, which allows the contaminants to diffuse from the liquid-vapor interface back to the bulk fluid and be convected away. The diffusion process is facilitated by the thinness of the membrane, which mitigates the clogging risk.
Conclusions

We propose a membrane-based evaporative cooling device for thermal management of high flux electronics. In order to determine an application-specific design and quantify the overall performance, we carried out a detailed thermal analysis. The analysis incorporates the non-equilibrium effects and the deviation from classical kinetic theory for the interfacial transport. Through the analysis, we identified two non-dimensional quantities, namely the interfacial heat transfer factor and the liquid transport factor, as important criteria for coolant selection. We modeled the overall thermal resistance across the liquid-vapor interface, membrane and the supporting microchannel structure, and the pressure drop associated with coolant supply through the micro/nanofluidic network.

A parametric sweep of critical geometries demonstrates the effect of each parameter on the device performance and a global optimization of device design results in a HTC of 0.0541 kW/cm²-K to dissipate a heat flux of 1 kW/cm². A non-dimensional analysis also demonstrates that for most state-of-the-art cooling techniques based on micro/nano-wicking structures, there is a qualitative trade-off between thermal performance and risk of dry-out. However, by applying detailed computational analysis and optimization for a particular fluid, one can design a device that meets both performance and reliability metrics successfully over a wide range of operating conditions. The proposed cooling device decouples these two factors by utilizing a thin nanoporous membrane supported on relatively thick and thermally conducting fluidic network. This work can potentially have an impact on thermal management of high flux power electronics, such as GaN HEMTs, by significantly reducing the near junction temperature (by > 40 K) compared to traditional single-phase microchannel cooling, due to a two-fold increase in the die-level heat transfer coefficient.

Acknowledgements
This work is supported by the DARPA ICECool Fundamentals program with Dr. Avram Bar-Cohen as the program manager. The authors also acknowledge Dr. Rong Xiao at Exxon Mobil Upstream Research Company, Dr. Ryan Enright at Bell Laboratories, Dublin and Prof. Rishi Raj at Indian Institute of Technology Patna for the helpful discussion and suggestions.
Figure 1  (a) Standard lay-out of the reference GaN HEMT described in Ref. [5]  (b) Schematic of the cross-section and boundary conditions for GaN HEMT with a silicon microchannel cooler. The temperature dependence is taken into account for thermal conductivities of GaN and SiC and the thermal boundary resistance between them [26]. The inward heat flux and the heat transfer coefficient for silicon microchannel cooler are adapted from Ref. [4]  (c) Cross-section and (d) bottom view schematic of proposed cooling device attached to the GaN HEMT die: liquid is routed into microchannels and wicks into nanopores of a membrane supported by channel walls; heat is conducted across the substrate, via the channel walls, within the membrane and to the liquid-vapor interface where evaporation occurs. The evaporated working fluid condenses at a condenser and is then circulated back to the inlet of the cooling device. (e) Temperature profile in the GaN HEMT including both the GaN die and the SiC substrate and (f) heat flux distribution at the backside of the SiC substrate when it is attached to a copper microchannel cooler with a heat transfer coefficient of 0.021 kW/cm²-K [4] rejecting heat to a 25 °C reservoir
Figure 2  (a) Schematic of interfacial transport across a nanopore in a unit cell. (b) Interfacial heat transfer coefficient from nanoporous membrane normalized over pore cross-section area as a function of temperature difference between evaporating surface and far field vapor ($T_\infty = 25 \, ^\circ C$) with $\bar{\sigma} = 1$ and $\phi = 0.2$ for different working fluids. (c) Effect of $\phi$ on $h_{in}$ normalized over pore cross-section area for R134a at select superheats with $T_\infty = 25 \, ^\circ C$. 
Figure 3  
(a) Boundary conditions for a device unit cell (the yellow dash box in Figure 1(e)): a uniform heat flux $q''$ is applied to the bottom of the unit cell while an evaporative heat transfer coefficient is assigned on top of the membrane where liquid can wick in. All other boundaries are assumed to be adiabatic. Both the working fluid and the solid material were assigned temperature-dependent thermal conductivities and the thermal transport in the channel wall and the membrane was considered as size-dependent. (b) Temperature profile in the unit cell for a reference design with $\phi = 0.2$, $d_p = 100$ nm, $t = 300$ nm, $w = 5$ μm, $AR = 1$ and $SF = 0.2$
Figure 4  Parametric study of $h_d$ (blue dash line) and $P_B^*$ (orange solid line) as functions of (a) porosity $\phi$, (b) pore diameter $d_p$, (c) membrane thickness $t$, (d) microchannel width $w$, (e) channel aspect ratio $AR$ and (f) channel wall solid fraction $SF$. 
Figure 5  Global optimization of device geometric design at \( \dot{q}'' = 1 \text{ kW/cm}^2 \): to maximize \( h_d \) while maintaining \( P_B^* > 0.6 \), the geometric parameters are designed as: \( \phi = 0.4 \), \( d_p = 120 \text{ nm} \), \( t = 450 \text{ nm} \), \( w = 4 \mu \text{m} \), \( AR = 2.5 \) and \( SF = 0.25 \). For this optimum design, \( h_d \) varies as a function of \( \dot{q}'' \) (inset).
Figure 6  (a) Temperature profile in the GaN HEMT die and (b) heat flux distribution at the backside of the cooler with implementation of the proposed cooling device
Reference


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